

ABSTRACT

The present invention relates to the technical field of semiconductor chip manufacturing, and in particular to a method and an apparatus for real-time monitoring of wafer warpage. During the thin film deposition on a wafer, the heating power change rate of each heating area on a heating tray is monitored in real time, wherein the heating tray includes at least two heating areas, each heating area is in a set constant temperature control state, the wafer is arranged on the at least two heating areas, and the wafer has a wafer area corresponding to each of the heating areas; whether the corresponding wafer area is detached from the heating tray is determined according to the heating power change rate. During the thin film deposition, the variation of wafer warpage can be monitored in real time by monitoring the variation of heating power, without the need for an additional measuring equipment.